

095456-0510

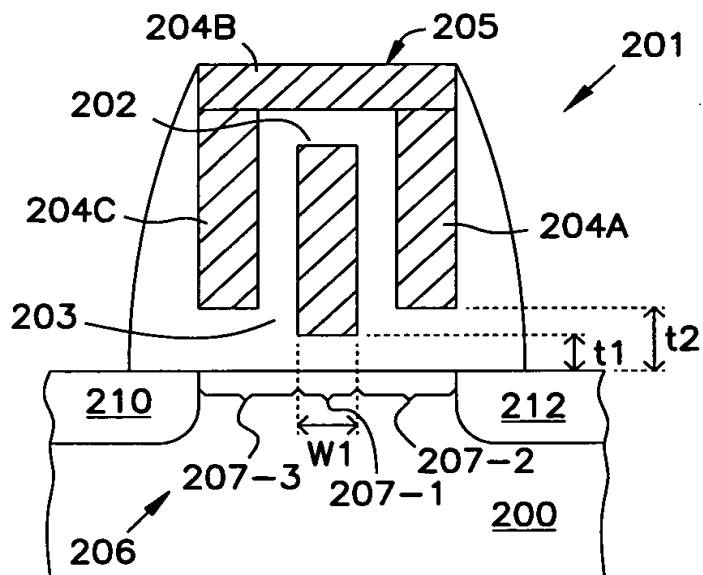


FIG. 2A

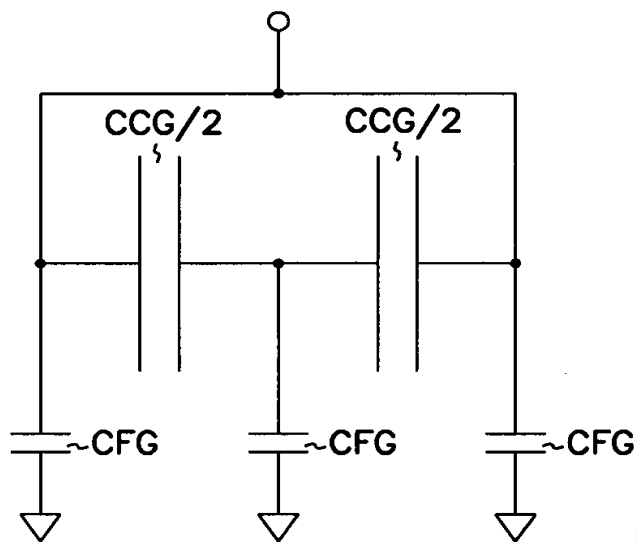


FIG. 2B

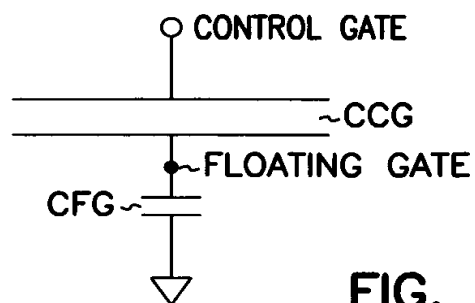


FIG. 2C

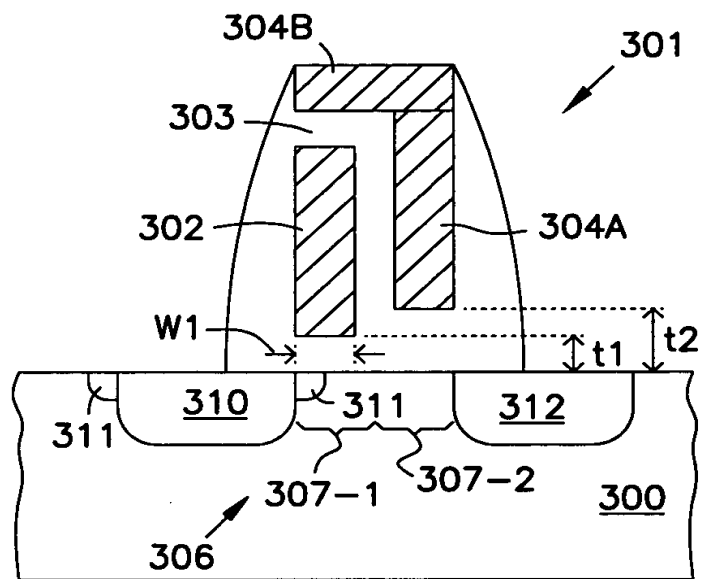


FIG. 3A

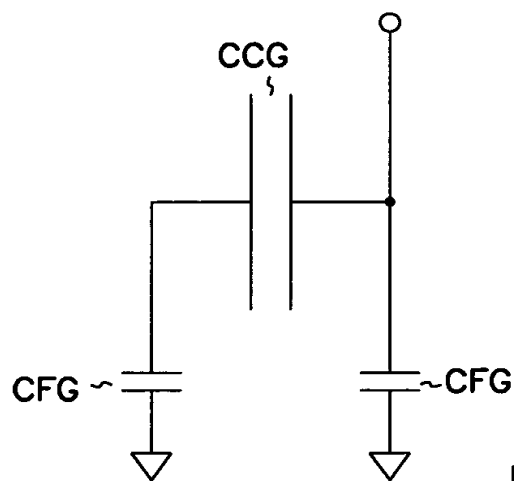


FIG. 3B

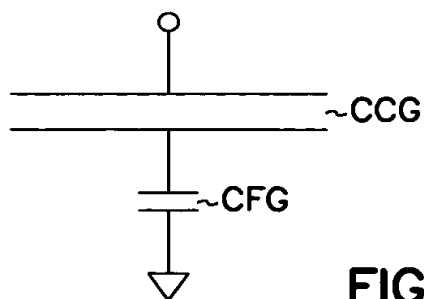
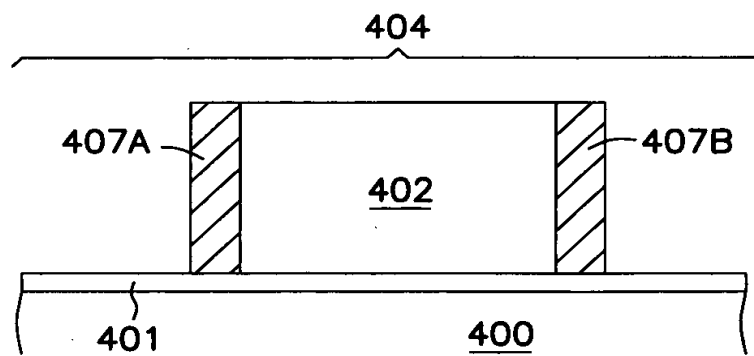
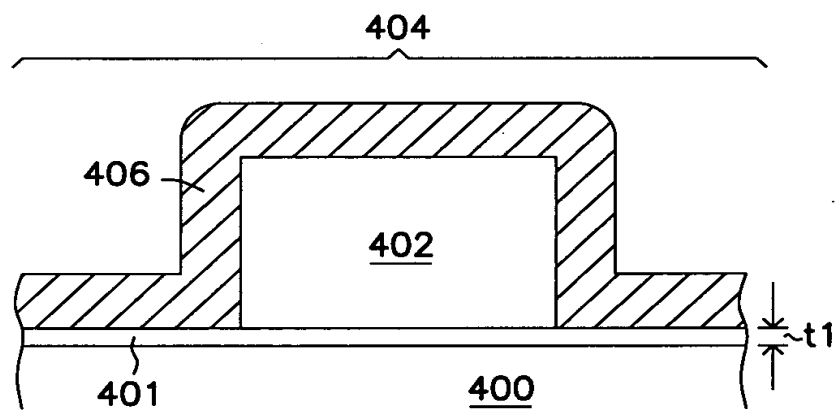
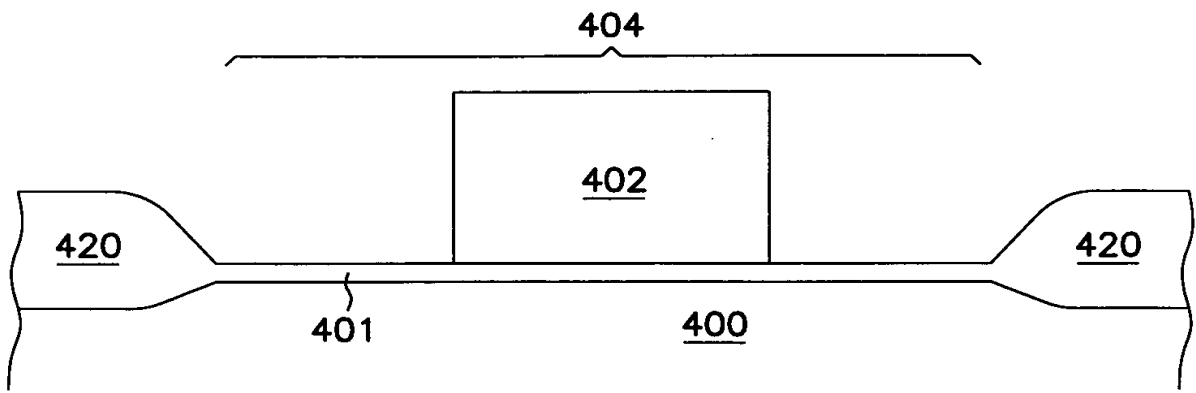
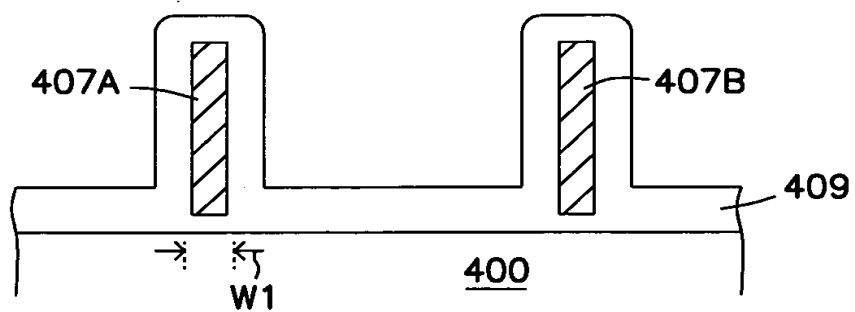
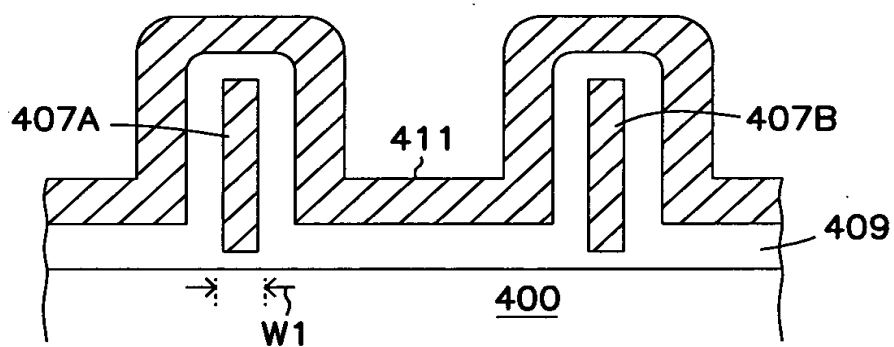


FIG. 3C





**FIG. 4D**



**FIG. 4E**

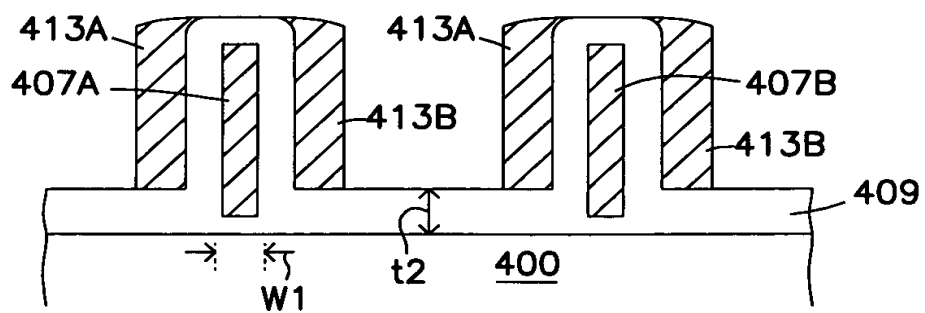


FIG. 4F

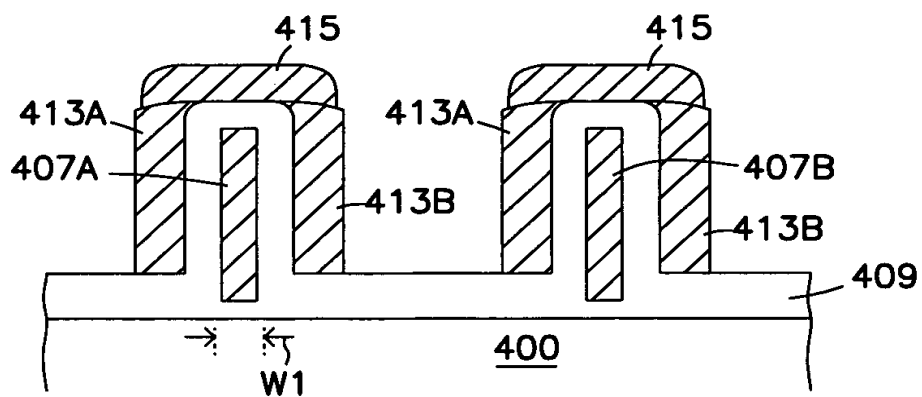


FIG. 4G

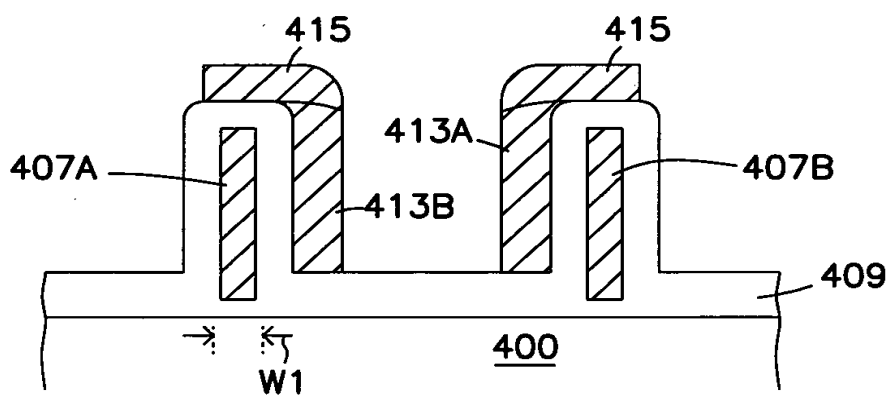


FIG. 4H

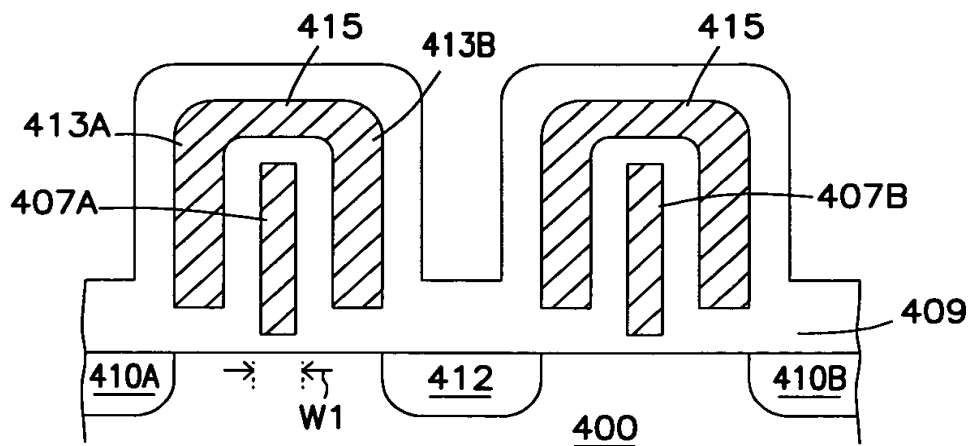
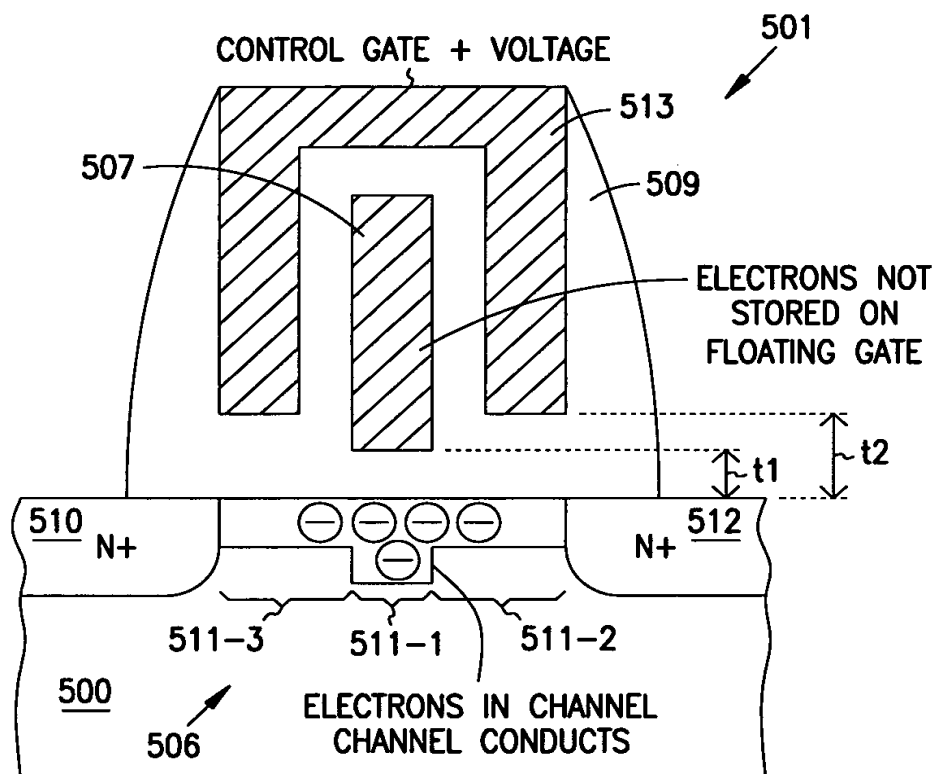
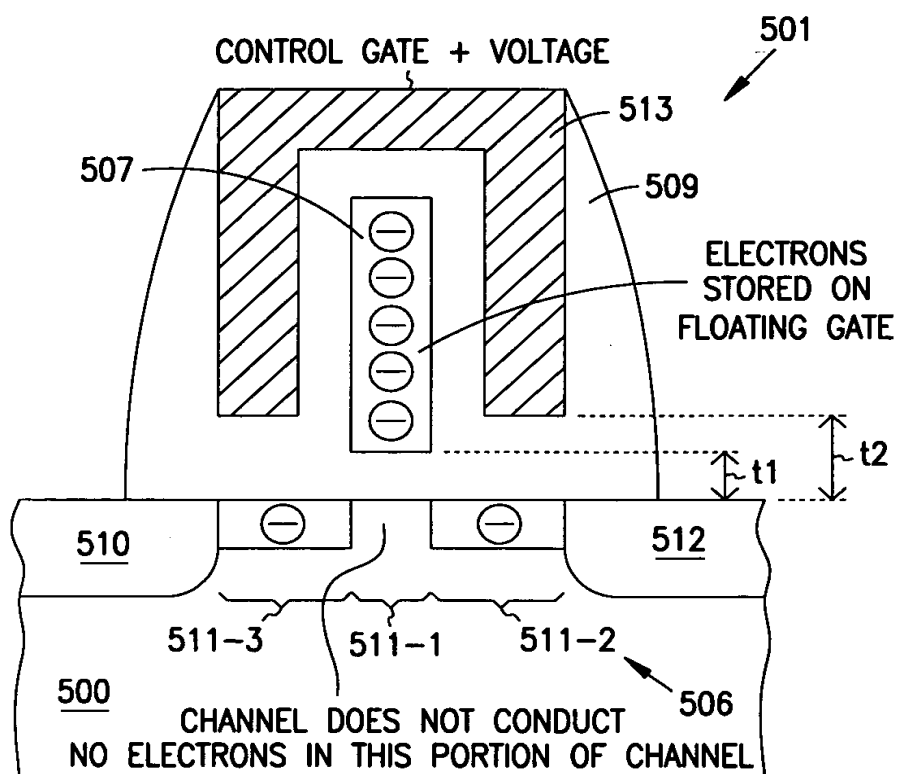


FIG. 4I

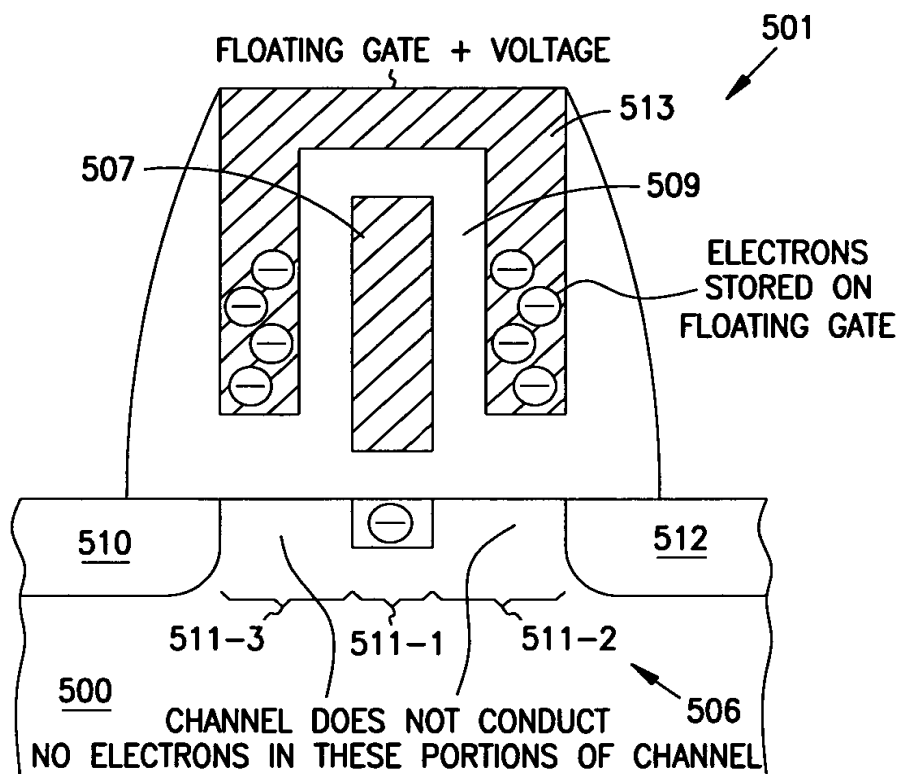


**FIG. 5A**



**FIG. 5B**

A cross-sectional view of a floating gate transistor 500. The device features a floating gate 507, which is a U-shaped structure with a central vertical bar, all filled with diagonal hatching. This floating gate is positioned above a channel conduct 509, which is a rectangular region also filled with diagonal hatching. The channel conduct is situated within a substrate 500. The substrate has N+ regions 510 and 512 on either side of the channel conduct. The floating gate is connected to a voltage source 501, indicated by an arrow. The channel conduct is connected to a voltage source 506, indicated by an arrow. The channel conduct is shown with five circles containing minus signs, representing electrons. The floating gate is shown with a label "ELECTRONS NOT STORED ON FLOATING GATE". The channel conduct is labeled "ELECTRONS IN CHANNEL CHANNEL CONDUCTS". The substrate is labeled "500". The N+ regions are labeled "510 N+" and "512 N+". The floating gate is labeled "507". The channel conduct is labeled "509". The voltage source 501 is labeled "501". The voltage source 506 is labeled "506". The channel conduct is divided into three regions: 511-3, 511-1, and 511-2.





001250 934350

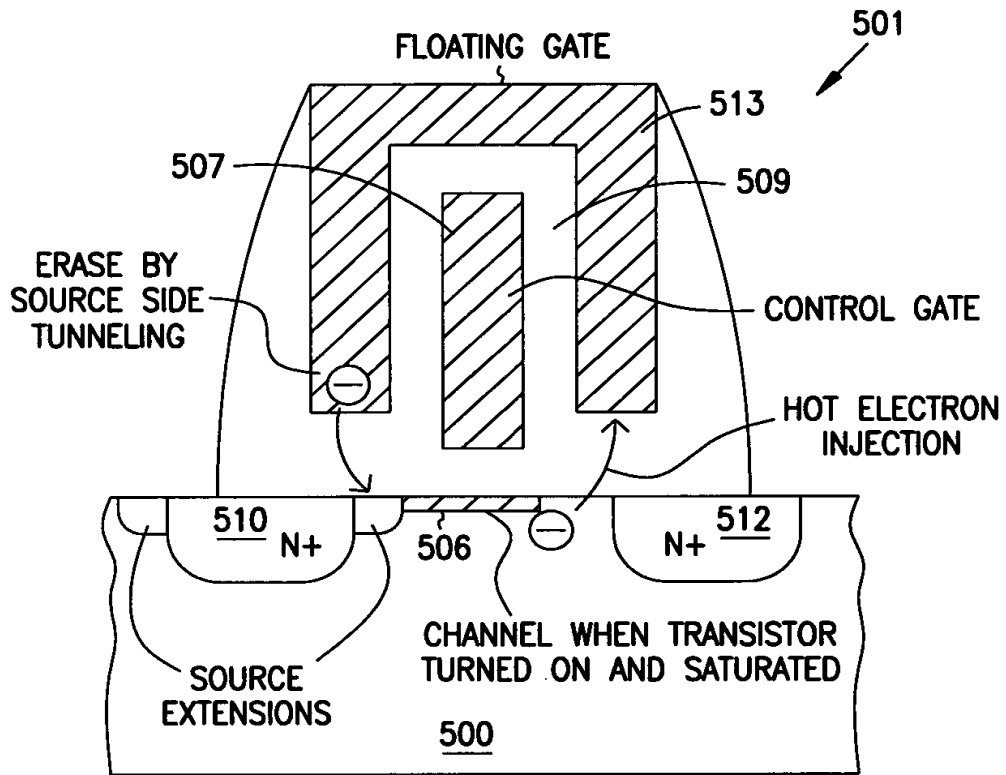


FIG. 5E

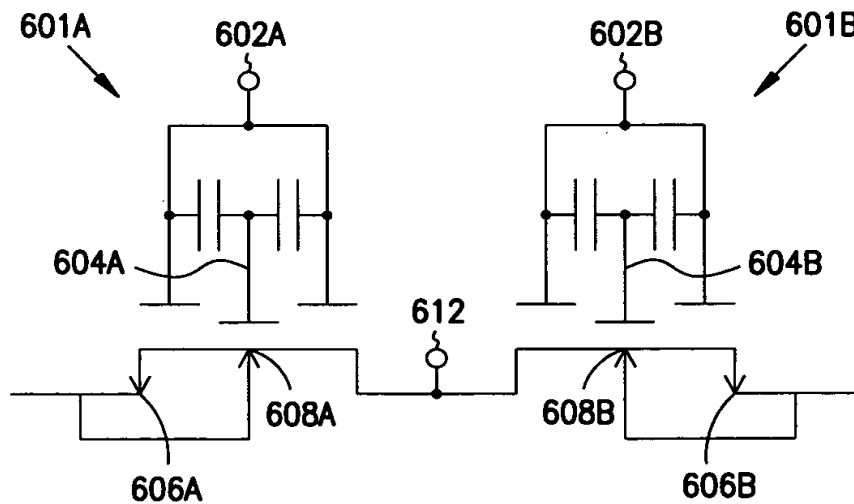


FIG. 6

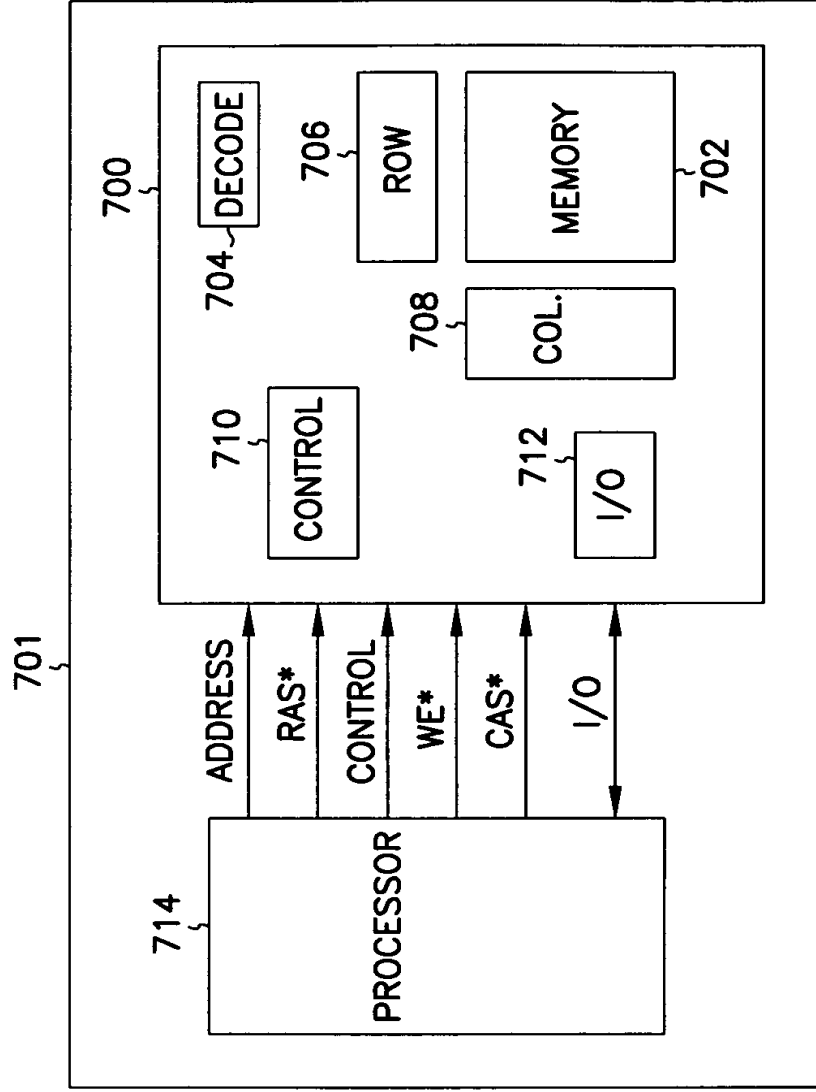


FIG. 7

007E50" 99518560

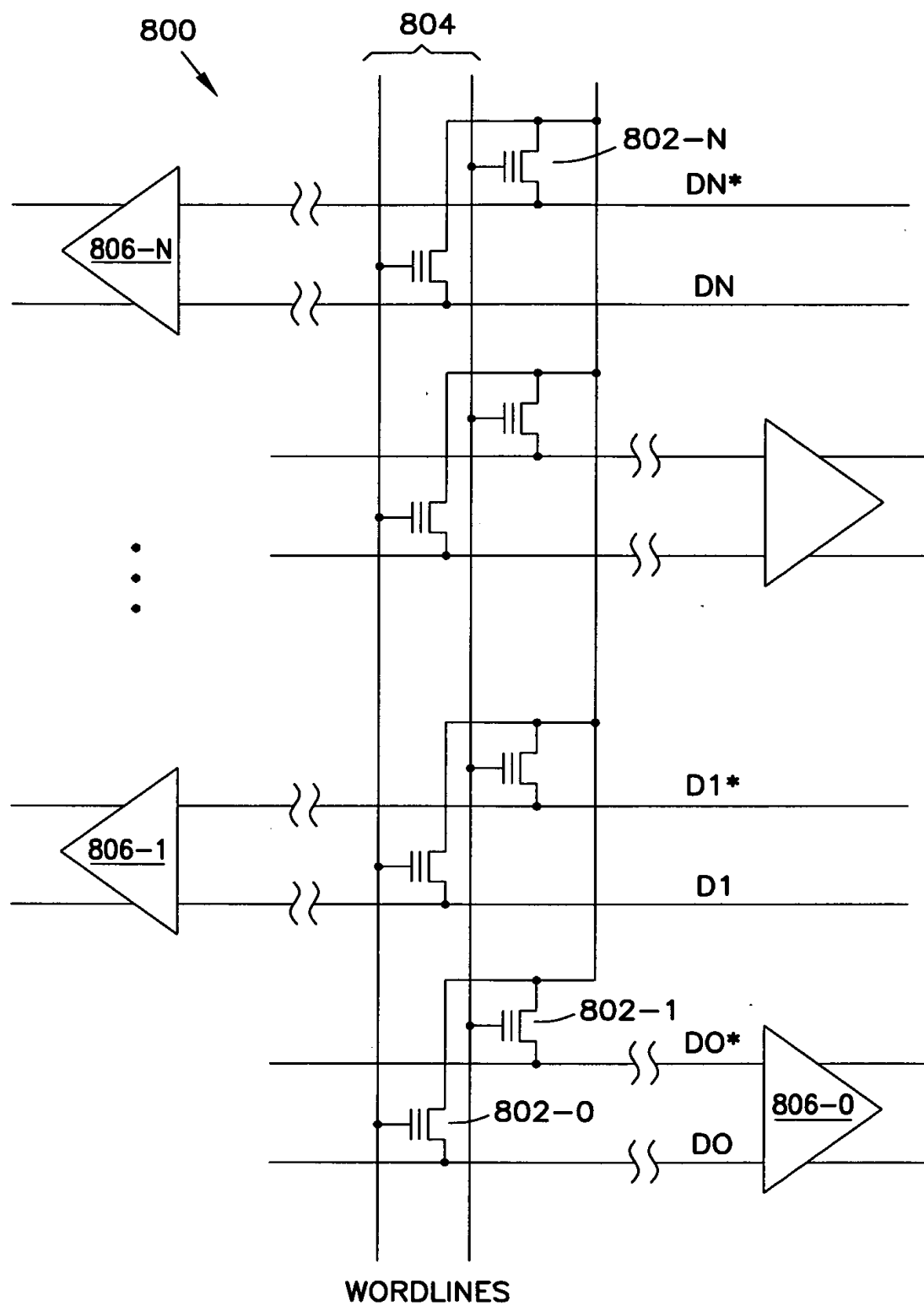


FIG. 8